



JST06 Series 6A TRIACs

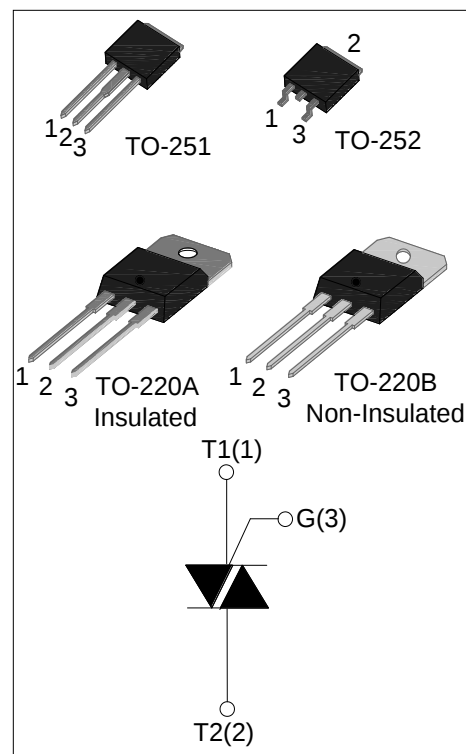
Rev.3.0

DESCRIPTION:

JST06 series triacs, with high ability to withstand the shock loading of large current, provide high dv/dt rate with strong resistance to electromagnetic interface. With high commutation performances, 3 quadrants products especially recommended for use on inductive load. JST06A provides insulation voltage rated at 2500V RMS from all three terminals to external heatsink complying with UL standards (File ref: E252906).

MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	6	A
V_{DRM}/V_{RRM}	600 and 800	V



ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		T_{stg}	-40 - 150	°C
Operating junction temperature range		T_j	-40 - 125	°C
Repetitive peak off-state voltage ($T_j=25^{\circ}\text{C}$)		V_{DRM}	600/800	V
Repetitive peak reverse voltage ($T_j=25^{\circ}\text{C}$)		V_{RRM}	600/800	V
Non repetitive surge peak Off-state voltage		V_{DSM}	$V_{DRM} + 100$	V
Non repetitive peak reverse voltage		V_{RSM}	$V_{RRM} + 100$	V
RMS on-state current	TO-251/ TO-252 TO-220B(Non-Ins) ($T_C=107^{\circ}\text{C}$)	$I_{T(RMS)}$	6	A
	TO-220A(Ins) ($T_C=100^{\circ}\text{C}$)			
Non repetitive surge peak on-state current (full cycle, $F=50\text{Hz}$)		I_{TSM}	60	A
I^2t value for fusing ($t_p=10\text{ms}$)		I^2t	18	A^2s

Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$)	dI/dt	50	A/ μ s
Peak gate current	I_{GM}	2	A
Average gate power dissipation	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	5	W

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant		Value				Unit
				TW	SW	CW	BW	
I_{GT}	$V_D=12\text{V } R_L=30\Omega$	I - II -III	MAX	5	10	35	50	mA
V_{GT}		I - II -III	MAX	1.5				V
V_{GD}	$V_D=V_{DRM} T_j=125^\circ\text{C}$ $R_L=3.3\text{K}\Omega$	I - II -III	MIN	0.2				V
I_L	$I_G=1.2I_{GT}$	I -III	MAX	10	15	50	70	mA
		II		15	25	60	80	
I_H	$I_{TM}=0.2\text{A}$		MAX	6	10	35	60	mA
dV/dt	$V_D=2/3V_{DRM}$ Gate Open $T_j=125^\circ\text{C}$		MIN	20	50	400	1000	V/ μ s

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V_{TM}	$I_{TM}=8.5\text{A } tp=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.55	V
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	5	μA
I_{RRM}		$T_j=125^\circ\text{C}$	1	mA

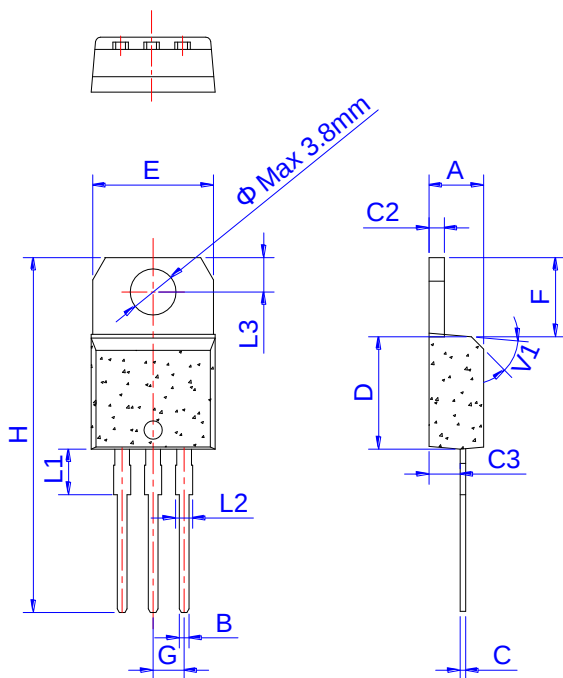
THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-251/ TO-252	3.5	$^\circ\text{C/W}$
		TO-220A(Ins)	3.9	
		TO-220B(Non-Ins)	2.4	

ORDERING INFORMATION

J	ST	06	B	-600	TW
JieJie Microelectronics Co.,Ltd	Triacs	$I_{T(RMS)}:6A$ H:TO-251 K:TO-252 A:TO-220A(Ins) B:TO-220B(Non-Ins)		600: $V_{DRM}/V_{RRM} \geq 600V$ 800: $V_{DRM}/V_{RRM} \geq 800V$	TW: $I_{GT1-3} \leq 5mA$ SW: $I_{GT1-3} \leq 10mA$ CW: $I_{GT1-3} \leq 35mA$ BW: $I_{GT1-3} \leq 50mA$

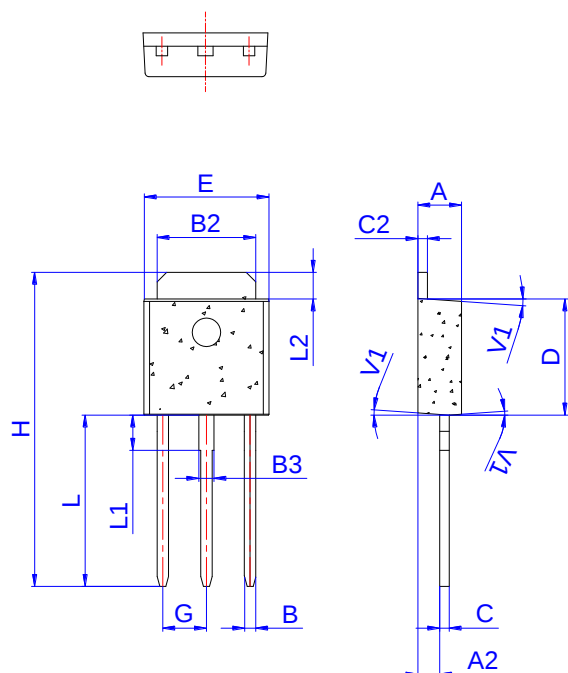
PACKAGE MECHANICAL DATA



TO-220A Ins

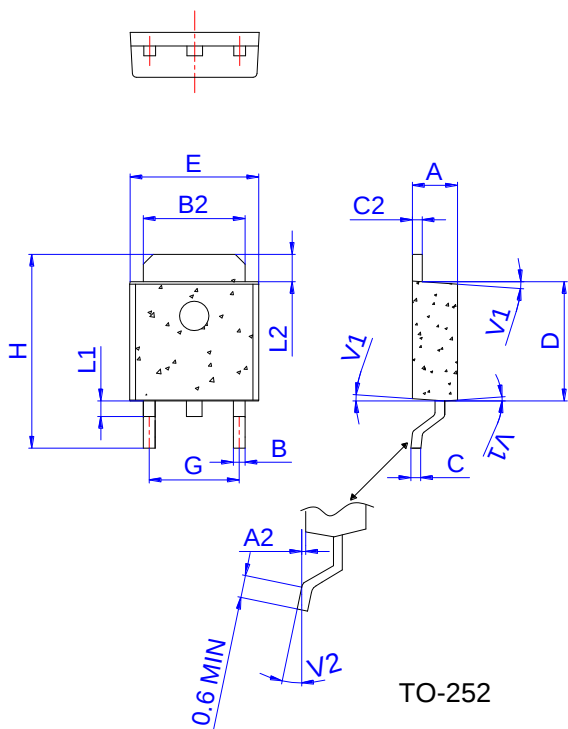
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.80		10.4	0.386		0.409
F	6.55		6.95	0.258		0.274
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.75			0.148	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	

PACKAGE MECHANICAL DATA



TO-251

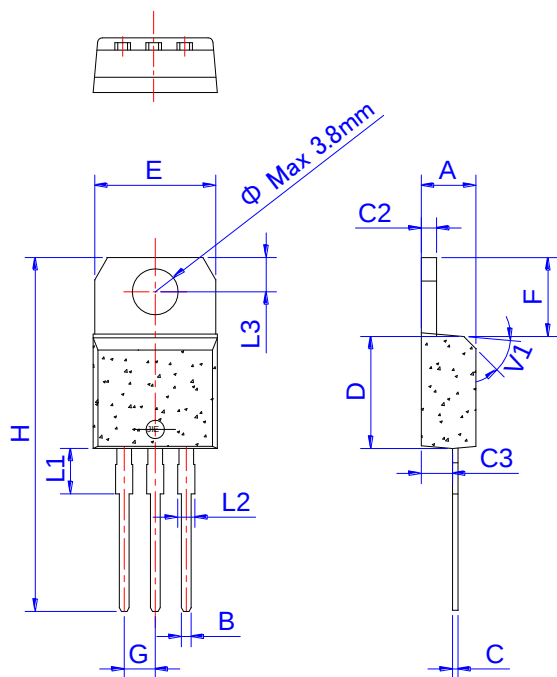
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.095
A2	0.90		1.20	0.035		0.047
B	0.55		0.65	0.022		0.026
B2	5.10		5.40	0.200		0.213
B3	0.76		0.85	0.030		0.033
C	0.45		0.62	0.018		0.024
C2	0.48		0.62	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.70	0.252		0.264
G		2.30			0.091	
H	16.0		17.0	0.630		0.669
L	8.90		9.40	0.350		0.370
L1	1.80		1.90	0.071		0.075
L2	1.37		1.50	0.054		0.059
V1		4°			4°	



TO-252

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.095
A2	0.03		0.23	0.001		0.009
B	0.55		0.65	0.022		0.026
B2	5.10		5.40	0.200		0.213
C	0.45		0.62	0.018		0.024
C2	0.48		0.62	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.70	0.252		0.264
G	4.40		4.70	0.173		0.185
H	9.35		10.6	0.368		0.417
L1	1.30		1.70	0.051		0.067
L2	1.37		1.50	0.054		0.059
V1		4°			4°	
V2	0°		8°	0°		8°

PACKAGE MECHANICAL DATA



TO-220B Non-Ins

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.60		10.4	0.378		0.409
F	6.20		6.60	0.244		0.260
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.75			0.148	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	

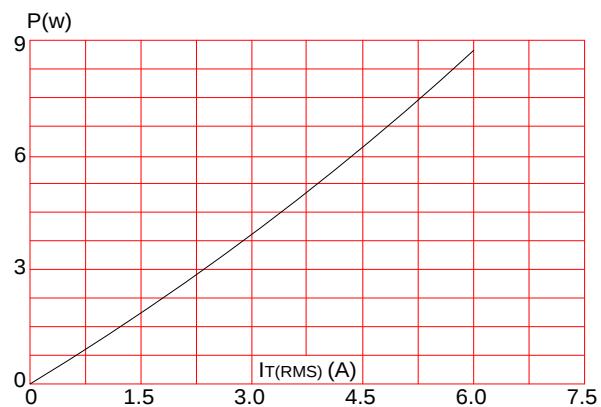
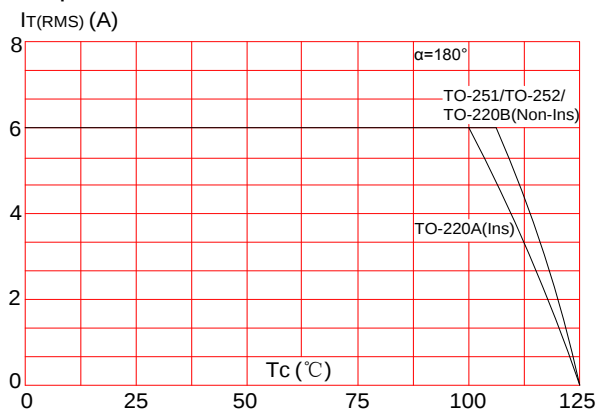
FIG.1 Maximum power dissipation versus RMS on-state current**FIG.2:** RMS on-state current versus case temperature

FIG.3: Surge peak on-state current versus number of cycles

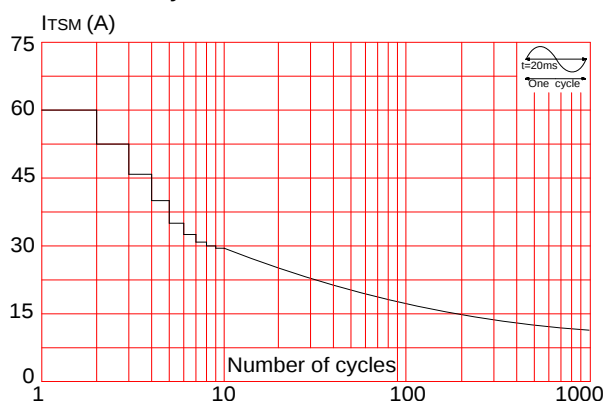


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t ($di/dt < 50\text{A}/\mu\text{s}$)

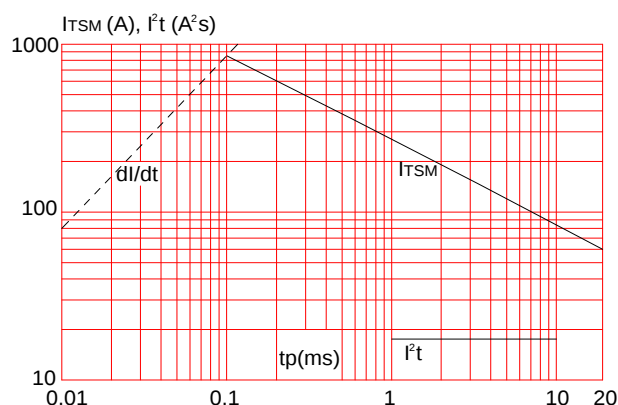


FIG.4: On-state characteristics (maximum values)

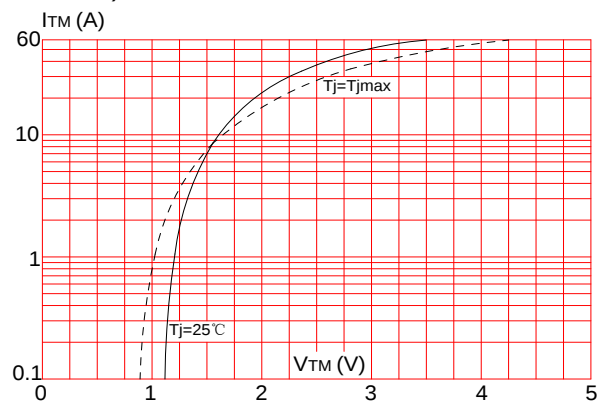
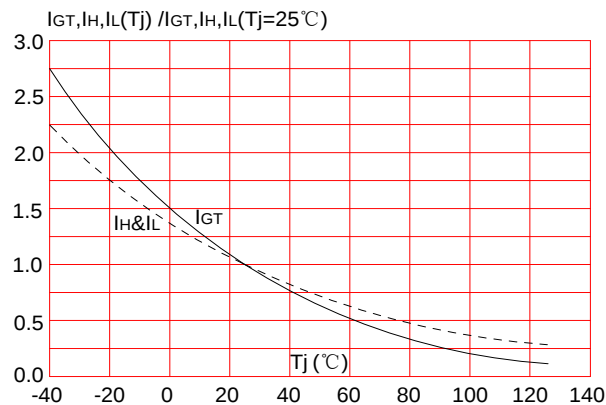


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature



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